

NTH4L023N065M3S

Silicon Carbide (SiC) MOSFET – EliteSiC, 23 mohm, 650 V, M3S, TO-247-4L

Product Overview

For complete documentation, see the data sheet.

The new family of 650V M3S planar SiC MOSFETs is optimized for fast switching applications. Planar technology works reliably with negative gate voltage drive and turn off spikes on the gate. This family has optimum performance when driven with 18V gate drive but also works well with 15V gate drive.

Features

- TO-247-4L Package with Kelvin source configuration
- Excellent FOM [= Rdson * Eoss]
- Ultra Low Gate Charge (QG(tot) = 69 nC)
- High Speed Switching with Low Capacitance (Coss = 153 pF)
- 15V to 18V Gate Drive
- New M3S technology: 23 mohm RDS(ON) with low Eon and Eoff losses
- 100% Avalanche Tested
- Halide Free and RoHS Compliant



Applications

- Industrial
- Cloud system

End Products

- UPS / ESS
- Solar
- EV Charger
- AI Data center

Part Electrical Specifications

Product	Status	Compliance	Famil y	Block ing Volta ge BV _{DS} s (V)	I _D (max) (A)	R _{DS(on)}) Typ @ 25°C (mΩ)	Q _g Total (nC)	Outp ut Capa citan ce (pF)	T _j Max (°C)	Pack age Type	Case Outli ne	MSL Type	MSL Tem p (°C)	Cont ainer Type	Cont ainer Qty.
NTH4L023N065M3S	Active, New	 	M3S	650	40	23	69	153	175	TO- 247- 4	340 C.J.P DF	NA	0	TUB E	450